

**Notice of References Cited**

Application/Control No.

09/735,217

Applicant(s)/Patent Under  
Reexamination  
ANDERSON, TIM

Examiner

Lisa A Kilday

Art Unit

2829

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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,274,518	08-2001	Yuri et al.	438/791
	B	US-6,533,874	03-2003	Vaudo et al.	148/33.5
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	WO-99-66565	12-1999	US	Kryliouk et al.	HO1L 33/00
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	"The effect of surface nitridation of LiGaO <sub>2</sub> substrates on the quality of MOVPE GaN", Kryoiouk et al., The 1997 Joint International meeting, Paris, August 31-September 5, 1997, Electrochemical Society, abstract No. 1830, pg. 2104
	V	"Dislocation distribution and subgrain structure of GaN films deposited on Sapphire by HVPE and MOVPE", Dunn et al., Mat. Res. Soc. Symp. Proc. Vol. 482, pg. 417-422, 1-5 Dec 1997
	W	"GaN substrates: growth and characterization", Kryliouk et al., 3rd International Conference on Nitride Semiconductors, Montpellier, France, 4-9 July 1999. Physica-Status-Solidi-A (Germany), vol.176, no.1, p.407-10, 16 Nov. 1999.
	X	"Thermal stability of MOCVD and HVPE GaN layers in H <sub>2</sub> , HCl, NH <sub>3</sub> and N <sub>2</sub> ", Mastro et al, Fourth International Conference on Nitride Semiconductors, Denver, CO, USA, 16-20 July 2001. Physica-Status-Solidi-A (Germany), vol.188, no.1, p.467-71, 16 Nov 2001

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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	U	"Large area GaN substrate", Kryliouk et al., 4th Intl. Workshop on expert evaluation and control of semiconductor materials and technologies (EXMATEC 98), Cardiff, UK 22-24 June 1998.
	V	"Growth of GAN single crystal substrate", Kryliouk et al., Materials Science Engineering, vol. 59, no. 1-3, pp. 6-11, 6/5/99
	W	"GaN grown by H-MOVPE on lattice-matched oxide and silicon substrates", Mastro et al., Materials Science Forum, vol. 389-93, pt. 2, pp. 1473-6, 2002.
	X	

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